

isc Silicon PNP Power Transistors

2SB337

DESCRIPTION

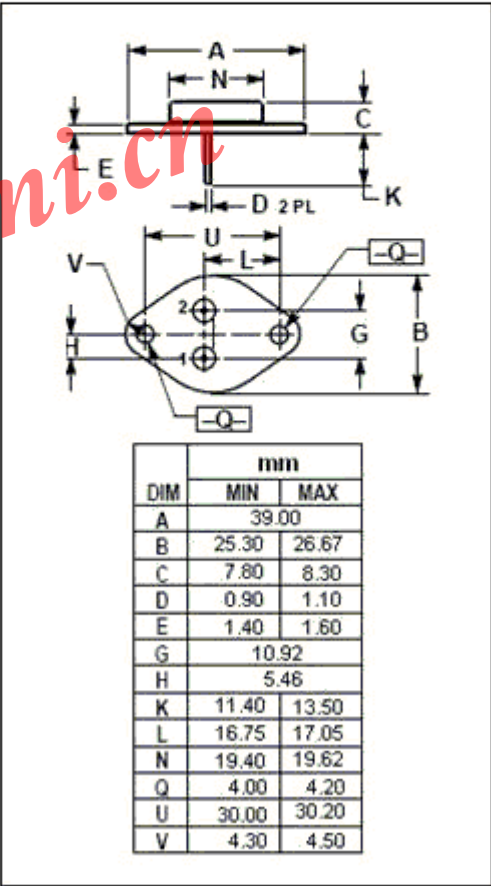
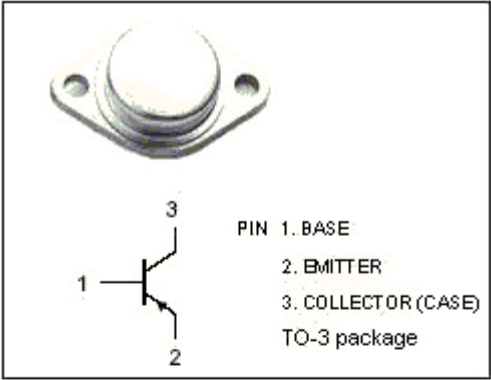
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = -0.29V(Typ.) @ I_C = -4A$
- High Power Dissipation-
: $P_C = 30W(Max) @ T_C = 55^{\circ}C$

APPLICATIONS

- Designed for audio frequency power output applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-40	V
V_{CER}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-10	V
I_C	Collector Current-Continuous	-7	A
I_E	Emitter Current-Continuous	7	A
I_B	Base Current-Continuous	-1	A
P_C	Collector Power Dissipation @ $T_C = 55^{\circ}C$	30	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$



isc Silicon PNP Power Transistors**2SB337****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CER}	Collector-Emitter Breakdown Voltage	I _C = -0.6A; R _{BE} = 68 Ω	-30			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -4A; I _B = -0.4A		0.29		V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -1A; V _{CE} = -2V		0.38		V
I _{CBO}	Collector Cutoff Current	V _{CB} = -30V; I _E = 0			-1.0	mA
h _{FE}	DC Current Gain	I _C = -1A; V _{CE} = -2V	50		165	

◆ **h_{FE} Classifications**

A	B
50-100	80-165

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